

# Alexander S Mayorov

## List of Publications by Year in descending order

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Version: 2024-02-01

29  
papers

7,236  
citations

361413

20  
h-index

454955

30  
g-index

31  
all docs

31  
docs citations

31  
times ranked

10174  
citing authors

#	ARTICLE	IF	CITATIONS
1	Ferroelectricity in hBN intercalated double-layer graphene. <i>Frontiers of Physics</i> , 2022, 17, .	5.0	6
2	Synthesis and properties of free-standing monolayer amorphous carbon. <i>Nature</i> , 2020, 577, 199-203.	27.8	250
3	Gate-Defined Quantum Confinement in InSe-Based van der Waals Heterostructures. <i>Nano Letters</i> , 2018, 18, 3950-3955.	9.1	40
4	Time-domain measurement of terahertz frequency magnetoplasmon resonances in a two-dimensional electron system by the direct injection of picosecond pulsed currents. <i>Applied Physics Letters</i> , 2016, 108, .	3.3	10
5	Terahertz plasmons in coupled two-dimensional semiconductor resonators. <i>Physical Review B</i> , 2015, 92, .	3.2	16
6	Excitation, detection and electrostatic manipulation of terahertz-frequency range plasmons in a two-dimensional electron system. <i>Scientific Reports</i> , 2015, 5, 15420.	3.3	21
7	On-chip THz-frequency tuneable plasmonic circuits. , 2015, , .		0
8	On-Chip Picosecond Pulse Detection and Generation Using Graphene Photoconductive Switches. <i>Nano Letters</i> , 2015, 15, 1591-1596.	9.1	33
9	Surface acoustic wave generation and detection using graphene interdigitated transducers on lithium niobate. <i>Applied Physics Letters</i> , 2014, 104, .	3.3	23
10	Raman Fingerprint of Aligned Graphene/h-BN Superlattices. <i>Nano Letters</i> , 2013, 13, 5242-5246.	9.1	102
11	Interaction phenomena in graphene seen through quantum capacitance. <i>Proceedings of the National Academy of Sciences of the United States of America</i> , 2013, 110, 3282-3286.	7.1	239
12	Cloning of Dirac fermions in graphene superlattices. <i>Nature</i> , 2013, 497, 594-597.	27.8	1,107
13	How Close Can One Approach the Dirac Point in Graphene Experimentally?. <i>Nano Letters</i> , 2012, 12, 4629-4634.	9.1	159
14	Impurities as a source of $\frac{1}{2}$ noise in graphene. <i>Physical Review B</i> , 2012, 85, .	3.2	66
15	Electron Tunneling through Ultrathin Boron Nitride Crystalline Barriers. <i>Nano Letters</i> , 2012, 12, 1707-1710.	9.1	724
16	Scanning gate microscopy on a graphene quantum point contact. <i>Physica E: Low-Dimensional Systems and Nanostructures</i> , 2012, 44, 1002-1004.	2.7	8
17	Interaction-Driven Spectrum Reconstruction in Bilayer Graphene. <i>Science</i> , 2011, 333, 860-863.	12.6	262
18	Dirac cones reshaped by interaction effects in suspended graphene. <i>Nature Physics</i> , 2011, 7, 701-704.	16.7	703

#	ARTICLE	IF	CITATIONS
19	Micrometer-Scale Ballistic Transport in Encapsulated Graphene at Room Temperature. Nano Letters, 2011, 11, 2396-2399.	9.1	1,440
20	Giant Nonlocality Near the Dirac Point in Graphene. Science, 2011, 332, 328-330.	12.6	255
21	Fluorographene: A Two-Dimensional Counterpart of Teflon. Small, 2010, 6, 2877-2884.	10.0	1,146
22	Density of States and Zero Landau Level Probed through Capacitance of Graphene. Physical Review Letters, 2010, 105, 136801.	7.8	202
23	Coulomb blockade in an open small ring with strong backscattering. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 1121-1123.	2.7	1
24	Weak localisation in bilayer graphene. Physica E: Low-Dimensional Systems and Nanostructures, 2008, 40, 1360-1363.	2.7	7
25	Conductance of p-n-p Graphene Structures with "Air-Bridge" Top Gates. Nano Letters, 2008, 8, 1995-1999.	9.1	168
26	Resistance fluctuations near the "metal-to-insulator" transition in the 2DEG in a Si-MOSFET. AIP Conference Proceedings, 2007, . .	0.4	1
27	Weak Localization in Bilayer Graphene. Physical Review Letters, 2007, 98, 176805.	7.8	205
28	Resonant tunnelling via two impurity levels in a vertical tunnelling nanostructure. Physica Status Solidi C: Current Topics in Solid State Physics, 2007, 4, 505-508.	0.8	1
29	1/f noise near the "metal-to-insulator transition" in the 2DEG in a Si-MOSFET. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 339-342.	0.8	1